

ABSTRACT OF THE DISCLOSURE

A resist pattern forming method using a coating and developing apparatus and an aligner being connected thereto which are controlled to form a resist film on a surface of a substrate with a base film and a base pattern formed thereon, followed by inspecting at least one of a plurality of measurement items selected from: reflection ratio and film thickness of the base film and the resist film, line width after a development, an accuracy that the base pattern matches with a resist pattern, a defect on the surface after the development, etc. A parameter subject to amendment is selected based on corresponding data of each measurement item, such as the film thickness of the resist and the line width after the development, and amendment of the parameter is performed. This results in a reduced workload of an operator, and an appropriate amendment can be performed.